

PNP general purpose transistor

PMBS3906

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- General purpose switching and amplification, e.g. telephony and professional communication equipment.

DESCRIPTION

PNP transistor in a SOT23 plastic package.
NPN complement: PMBS3904.

MARKING

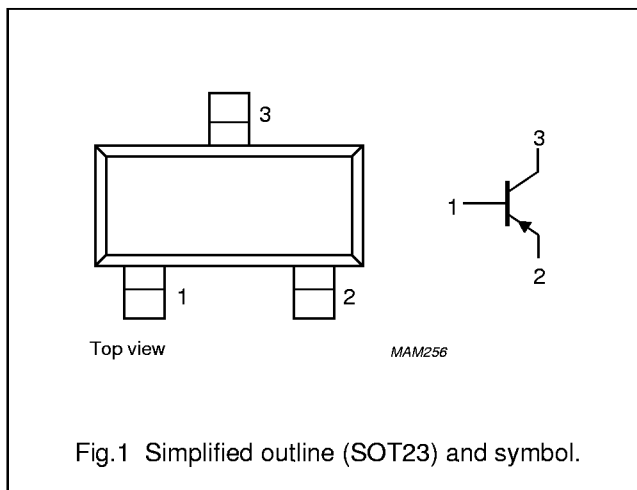
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMBS3906	*O6

Note

1. * = p : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	−40	V
V_{CEO}	collector-emitter voltage	open base	—	−40	V
V_{EBO}	emitter-base voltage	open collector	—	−5	V
I_C	collector current (DC)		—	−100	mA
I_{CM}	peak collector current		—	−200	mA
I_{BM}	peak base current		—	−200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	—	250	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		—	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = -30\text{ V}$	–	–50	nA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = -5\text{ V}$	–	–50	nA
h_{FE}	DC current gain	$V_{CE} = -1\text{ V}$; (see Fig.2) $I_C = -0.1\text{ mA}$ $I_C = -1\text{ mA}$ $I_C = -10\text{ mA}$ $I_C = -50\text{ mA}$; note 1 $I_C = -100\text{ mA}$; note 1	60 80 100 60 30	– – 300 – –	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}$; $I_B = -1\text{ mA}$	–	–250	mV
		$I_C = -50\text{ mA}$; $I_B = -5\text{ mA}$; note 1	–	–400	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}$; $I_B = -1\text{ mA}$	–	–850	mV
		$I_C = -50\text{ mA}$; $I_B = -5\text{ mA}$; note 1	–	–950	mV
C_c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -5\text{ V}$; $f = 100\text{ MHz}$	–	4.5	pF
C_e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = -0.5\text{ V}$; $f = 100\text{ MHz}$	–	12	pF
f_T	transition frequency	$I_C = -10\text{ mA}$; $V_{CE} = -20\text{ V}$; $f = 100\text{ MHz}$	150	–	MHz
F	noise figure	$I_C = -100\text{ }\mu\text{A}$; $V_{CE} = -5\text{ V}$; $R_S = 1\text{ k}\Omega$; $f = 10\text{ Hz}$ to 15.7 kHz ;	–	4	dB

Switching times (between 10% and 90% levels); (see Fig.3)

t_{on}	turn-on time	$I_{Con} = -10\text{ mA}$; $I_{Bon} = -1\text{ mA}$; $I_{Boff} = 1\text{ mA}$	–	100	ns
t_d	delay time		–	50	ns
t_r	rise time		–	50	ns
t_{off}	turn-off time		–	700	ns
t_s	storage time		–	600	ns
t_f	fall time		–	100	ns

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

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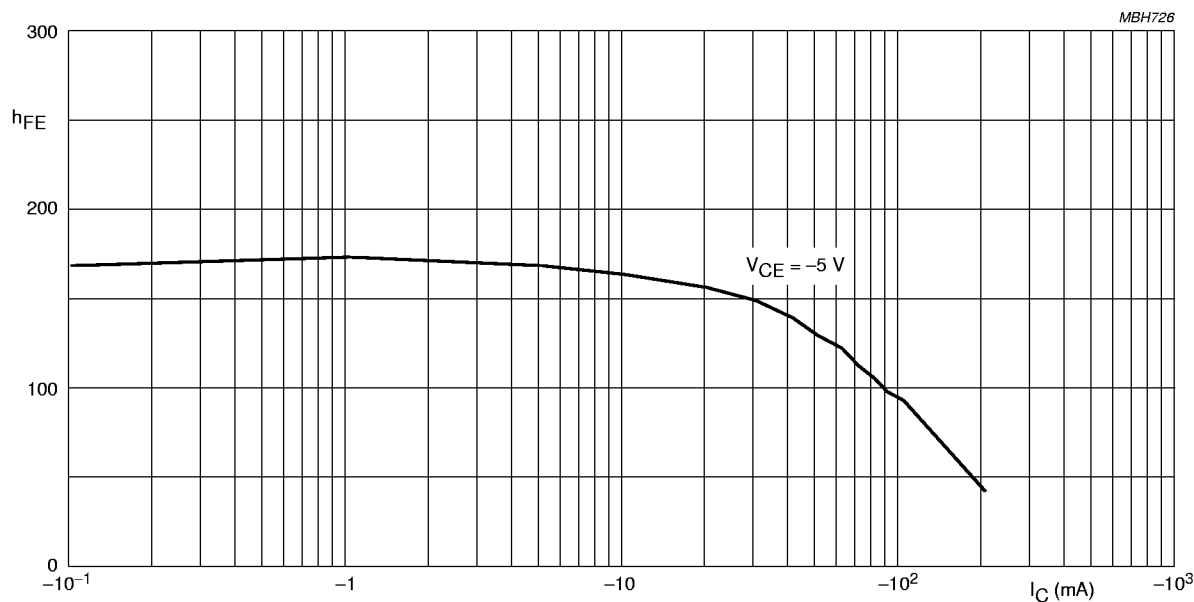
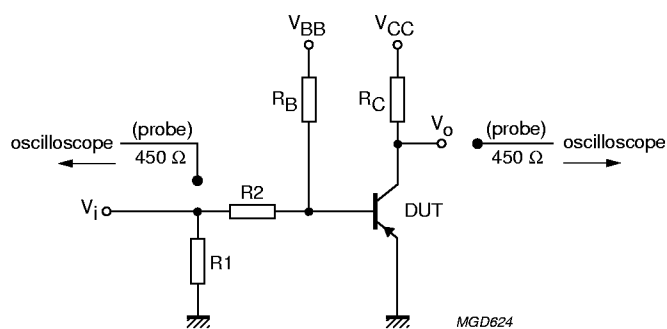


Fig.2 DC current gain; typical values.



$V_i = -5\text{ V}$; $T = 500\text{ }\mu\text{s}$; $t_p = 10\text{ }\mu\text{s}$; $t_r = t_f \leq 3\text{ ns}$.
 $R_1 = 56\text{ }\Omega$; $R_2 = 2.5\text{ k}\Omega$; $R_B = 3.9\text{ k}\Omega$; $R_C = 270\text{ }\Omega$.
 $V_{BB} = 1.9\text{ V}$; $V_{CC} = 3\text{ V}$.
 Oscilloscope input impedance $Z_i = 50\text{ }\Omega$.

Fig.3 Test circuit for switching times.

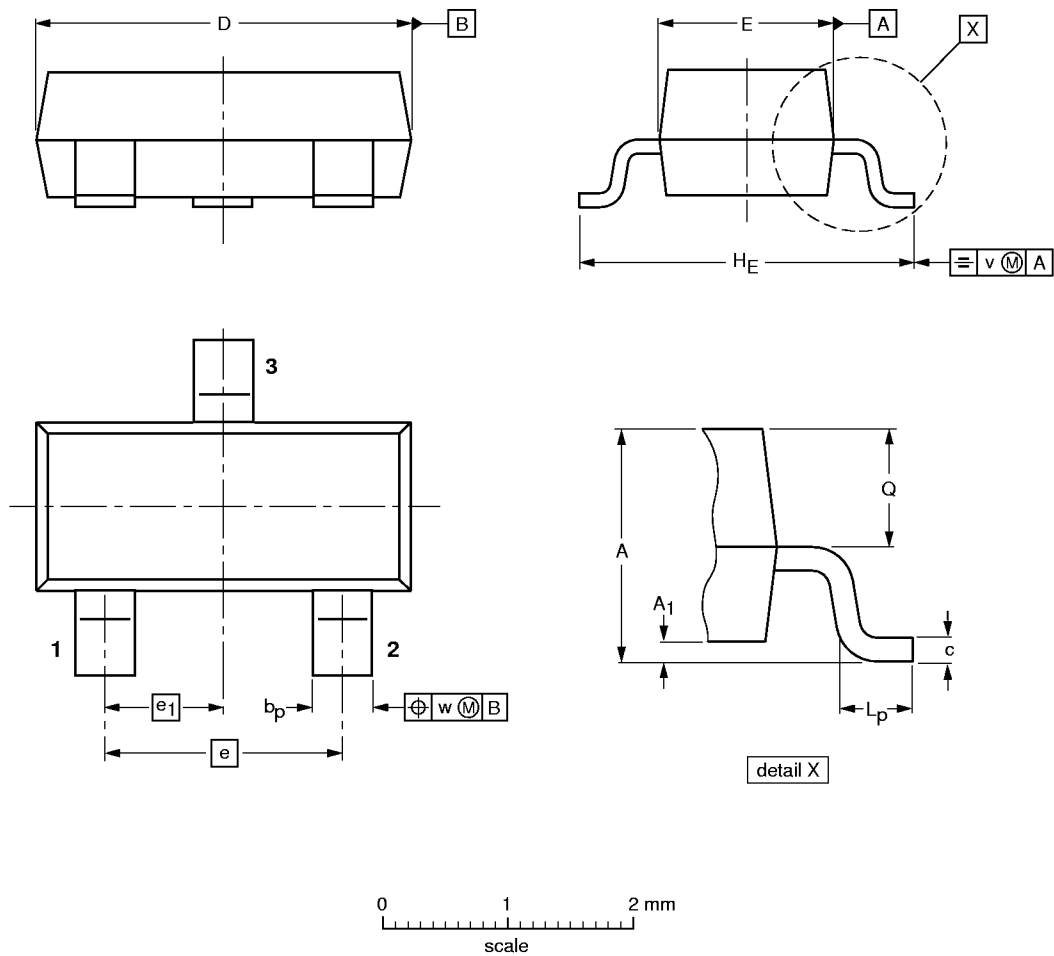
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23						97-02-28